

## SiC Power MOSFET

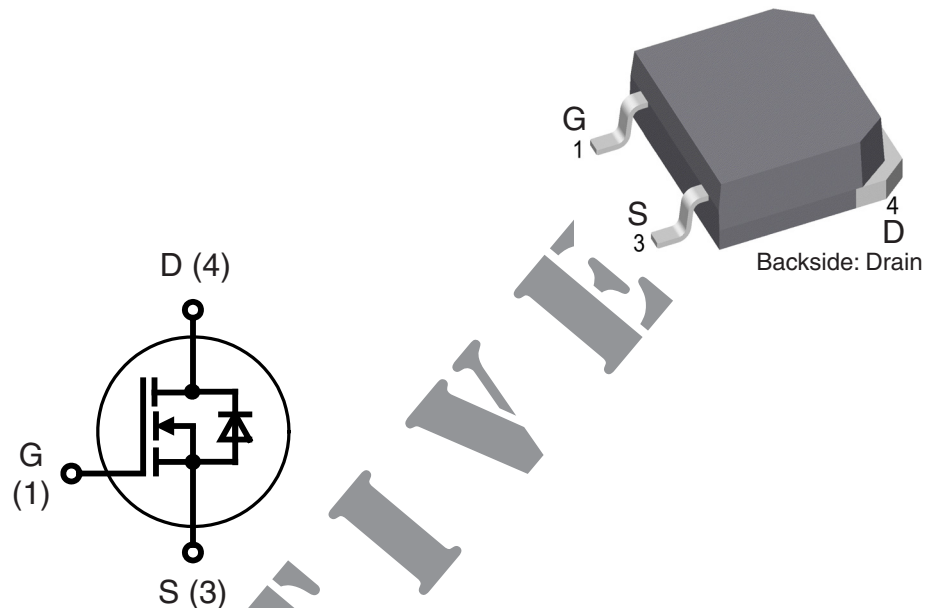
$$I_{D25} = 90 \text{ A}$$

$$V_{DSS} = 1200 \text{ V}$$

$$R_{DS(on) \text{ max}} = 34 \text{ m}\Omega$$

## Single MOSFET

Part number  
MCB60I1200TZ

**Features / Advantages:**

- High speed switching with low capacitances
- High blocking voltage with low  $R_{DS(on)}$
- Easy to parallel and simple to drive
- Avalanche ruggedness
- Resistant to latch-up

**Applications:**

- Solar inverters
- High voltage DC/DC converters
- Motor drives
- Switch mode power supplies
- UPS
- Battery chargers
- Induction heating

**Package:** TO-268AA (D3Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

**Terms & Conditions of usage**

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

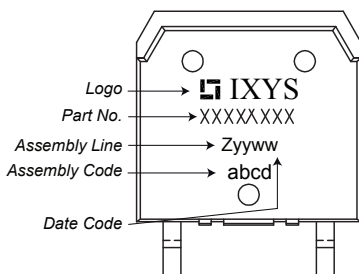
MOSFET				Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.		
$V_{DS}$	drain source breakdown voltage				1200		V
$V_{GS(M)}$	max transient gate source voltage		-10		+25		V
$V_{GS}$	continous gate source voltage	recommended operational value	-5		+20		V
$I_{D25}$	drain current				90		A
$I_{D80}$					70		A
$I_{D100}$					60		A
$R_{DS(on)}$	static drain source on resistance	$I_D = 50 \text{ A}; V_{GS} = 20 \text{ V}$		25 43 52	34		mΩ mΩ mΩ
$V_{GS(th)}$	gate threshold voltage	$I_D = 15 \text{ mA}; V_{DS} = 10 \text{ V}$	2.0	2.6 2.1	4.0		V V
$I_{DSS}$	drain source leakage current	$V_{DS} = 1200 \text{ V}; V_{GS} = 0 \text{ V}$		2	100		μA
$I_{GSS}$	gate source leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}$			0.6		μA
$R_G$	internal gate resistance				1.1		Ω
$C_{iss}$	input capacitance	$V_{DS} = 1000 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		2790		pF
$C_{oss}$	output capacitance				220		pF
$C_{rss}$	reverse transfer (Miller) capacitance				15		pF
$Q_g$	total gate charge	$V_{DS} = 800 \text{ V}; I_D = 50 \text{ A}; V_{GS} = -5/20 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$		160		nC
$Q_{gs}$	gate source charge				46		nC
$Q_{gd}$	gate drain (Miller) charge				50		nC
$t_{d(on)}$	turn-on delay time	Inductive switching $V_{DS} = 800 \text{ V}; I_D = 50 \text{ A}$ $V_{GS} = -5/20 \text{ V}; R_G = 2 \text{ } \Omega \text{ (external)}$	$T_{VJ} = 25^\circ\text{C}$				ns
$t_r$	current rise time						ns
$t_{d(off)}$	turn-off delay time						ns
$t_f$	current fall time						ns
$E_{on}$	turn-on energy per pulse						mJ
$E_{off}$	turn-off energy per pulse						mJ
$E_{rec(off)}$	reverse recovery losses at turn-off						mJ
$R_{thJC}$	thermal resistance junction to case	with heatsink compound; IXYS test setup <sup>1)</sup>		0.38	0.27		K/W K/W
$R_{thJH}$	thermal resistance junction to heatsink						

<sup>1)</sup> part is mounted directly on heat sink

Source-Drain Diode				Ratings					
Symbol	Definitions	Conditions	min.	typ.	max.				
$I_{S25}$	continuous source current	$V_{GS} = -5 \text{ V}$					A		
$I_{S100}$								A	
$V_{SD}$	forward voltage drop	$I_F = 25 \text{ A}; V_{GS} = -5 \text{ V}$		4.0 3.5			V V		
$t_{rr}$	reverse recovery time	$V_{GS} = -5 \text{ V}; I_F = 50 \text{ A}$ $V_R = 800 \text{ V}; -di_F/dt = 1000 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$				ns		
$Q_{RM}$	reverse recovery charge (intrinsic diode)						410		nC
$I_{RM}$	max. reverse recovery current						13.5		A

**Package TO-268AA (D3Pak-HV)**

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
$I_{RMS}$	RMS current	per terminal				A
$T_{stg}$	storage temperature		-40		150	°C
$T_{op}$	operation temperature		-40		150	°C
$T_{vJ}$	virtual junction temperature		-40		175	°C
<b>Weight</b>				4		g
$F_C$	mounting force with clip		20		120	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	9.4			mm
$d_{Spb/Appb}$		terminal to backside	5.6			mm

**Product Marking**

**Part number**

M = Mosfet  
 C = SiC MOSFET  
 B = Generation 2  
 60 = Current Rating [A]  
 I = Single Mosfet  
 1200 = Reverse Voltage [V]  
 TZ = TO-268AA (D3Pak) (2HV)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MCB60I1200TZ	MCB60I1200TZ	Tube	30	515522